



AMENDMENT TRANSMITTAL LETTER

Docket No.
SON-1745

Application No. 09/512,336	Filing Date February 24, 2000	Examiner K. Chen	Art Unit 1765
-------------------------------	----------------------------------	---------------------	------------------

Applicant(s): Seiichi FUKUDA

Invention: DRY ETCHING METHOD AND METHOD OF MANUFACTURING SEMICONDUCTOR APPARATUS

TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

CLAIMS AS AMENDED

	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	4	- 20 =		x	0.00
Independent Claims	2	- 3 =		x	0.00
Multiple Dependent Claims (check if applicable)					<input type="checkbox"/>
Other fee (please specify):					
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:					0.00

Large Entity

Small Entity

No additional fee is required for this amendment.

Please charge Deposit Account No. _____ in the amount of \$ _____.
A duplicate copy of this sheet is enclosed.

A check in the amount of \$ _____ to cover the filing fee is enclosed.

Payment by credit card. Form PTO-2038 is attached.

The Commissioner is hereby authorized to charge and credit Deposit Account No. 18-0013 as described below. A duplicate copy of this sheet is enclosed.

Credit any overpayment.

Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.

1 42,316
Ronald P. Kananen
Attorney Reg. No.: 24,104

Dated: November 14, 2002

RADER, FISHMAN & GRAUER PLLC
Lion Building
1233 20th Street N.W., Suite 501
Washington, DC 20036
(202) 955-3750

RECEIVED
NOV 18 2002
TC 1700



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of
Seiichi FUKUDA

Serial No. 09/512,336

Filed: February 24, 2000

For: DRY ETCHING METHOD AND
METHOD OF MANUFACTURING
SEMICONDUCTOR APPARATUS

Group Art Unit: 1765

Examiner: K. Chen

RECEIVED
NOV 18 2002
TC 1700

SECOND AMENDMENT AFTER FINAL UNDER 37 C.F.R § 1.116

BOX AF

Commissioner for Patents
Washington, DC 20231

Sir:

This is a second amendment following the final Office Action dated July 9, 2002. Please amend the application as follows.

IN THE CLAIMS:

Please amend claims 1 and 4 as shown in the attached Appendix. A clean version of the claims is presented below.

1. (amended) A dry etching method comprising the step of:
dry-etching a formed film of tungsten in its entirety as
originally formed using only a single mixed gas including a
fluorine-containing gas that includes a compound having
fluorine and carbon in a molecule, chlorine or hydrogen
bromide, oxygen, and nitrogen,